Koji Nakayama

List of Publications by Year
in descending order

16	181	1651377 6	1526636 10
papers	citations	h-index	g-index

16	16	16	150
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Epitaxial growth and characterization of thick multi-layer 4H-SiC for very high-voltage insulated gate bipolar transistors. Journal of Applied Physics, 2015, 118, .	1.1	13
2	Open circuit voltage decay characteristics of 4H-SiC pâ€“iâ€“n diode with carbon implantation. Japanese Journal of Applied Physics, 2014, 53, 04EP08.	0.8	11
3	Minimum gate trigger current degradation in 4.5 kV 4H-SiC commutated gate turn-off thyristor. Japanese Journal of Applied Physics, 2014, 53, 044101.	0.8	4
4	13-kV, 20-A 4H-SiC PiN Diodes for Power System Applications. Materials Science Forum, 2014, 778-780, 855-858.	0.3	6
5	Conductivity Degradation of 4H-SiC pâ€“iâ€“n Diode with In-Grown Stacking Faults. Japanese Journal of Applied Physics, 2013, 52, 04CP10.	0.8	10
6	Transient Electrical Characteristics of Electron Irradiated High Blocking Voltage 4H-SiC Pin Diode. Materials Science Forum, 2012, 717-720, 965-968.	0.3	1
7	Electrical Characteristics of 4H-SiC Pin Diode with Carbon Implantation or Thermal Oxidation. Materials Science Forum, 2012, 717-720, 989-992.	0.3	1
8	Characteristics of a 4H-SiC Pin Diode With Carbon Implantation/Thermal Oxidation. IEEE Transactions on Electron Devices, 2012, 59, 895-901.	1.6	35
9	Drift Phenomena of Forward and Reverse Recovery Characteristics in 0001 4H-SiC pâ€“iâ€“n Diode. Japanese Journal of Applied Physics, 2011, 50, 04DF04.	0.8	0
10	Component Technologies for Ultra-High-Voltage 4H-SiC pin Diode. Materials Science Forum, 2011, 679-680, 535-538.	0.3	11
11	Annealing effects on single Shockley faults in 4H-SiC. Applied Physics Letters, 2006, 89, 062104.	1.5	74
12	SiC Zener Diode for Gate Protection of 4.5 kV SiCGT. Materials Science Forum, 0, 679-680, 559-562.	0.3	0
13	Lifetime Control of 4.5 kV SiCGT by High-Energy Electron Irradiation. Materials Science Forum, 0, 679-680, 718-721.	0.3	1
14	Simulation of TEDREC Phenomena for 4H-SiC Pin Diode with p/n Type Drift Layer. Materials Science Forum, 0, 740-742, 1107-1110.	0.3	2
15	Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT. Materials Science Forum, 0, 778-780, 135-138.	0.3	11
16	High Voltage and Fast Switching Reverse Recovery Characteristics of 4H-SiC PiN Diode. Materials Science Forum, 0, 778-780, 841-844.	0.3	1